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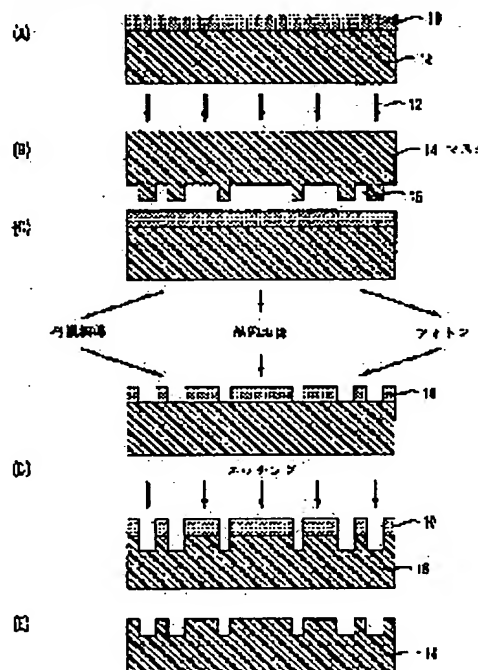
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## (54) PROCESS FOR PRODUCING DEVICE WITH FULLERENE-CONTAINING RESIST MATERIAL

(57)Abstract:

PURPOSE: To form a thin resist film by a dry method with a fullerene-contg. resist material in a lithographic process for producing a device.

CONSTITUTION: A fullerene-contg. resist material is deposited on a substrate 18 by a dry method to form a thin resist film 10 on the substrate 18. This resist film 10 is selectively exposed to form an image and the film 10 is patterned by development. The pattern of the film 10 is then transferred to the inside of the substrate 18 by reactive ion etching or other applicable technique.



## LEGAL STATUS

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